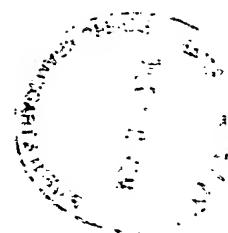


PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2003-243320
(43)Date of publication of application : 29.08.2003



(51)Int.CI.

H01L 21/265

(21)Application number : 2002-357059
(22)Date of filing : 09.12.2002

(71)Applicant : USHIO INC
(72)Inventor : MIYAUCHI KOJI
OOWADA TATSUSHI

(30)Priority

Priority number : 2001379762 Priority date : 13.12.2001 Priority country : JP

(54) METHOD OF HEAT-TREATING SEMICONDUCTOR WAFER

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method of heat-treating semiconductor wafer by which a semiconductor wafer which is an object to be treated can be heat-treated without breakage.
SOLUTION: In this method of the heat-treating semiconductor wafer, the semiconductor wafer is heat-treated by means of a flash light radiating means constituted of a flashing light radiating lamp after the wafer is preheated to a prescribed temperature by means of a preheating means. The preheating temperature is controlled so that a maximum tensile stress of the semiconductor wafer may not reach a threshold tensile stress of the wafer itself when the wafer is heated by means of the flashing light radiating lamp.

LEGAL STATUS

[Date of request for examination] 03.09.2004

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]